BF397

PNP SILICON TRANSISTOR

BF397 is PNP silicon transistor designed for high voltage applications.

TO-92F

CBE

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	90V
Collector-Emitter Voltage	VCEO	90V
Emitter-Base Voltage	VEBO	6V
Total Power Dissipation	Ptot	625mW
Collector Current	IC	100mA
Operating Junction & Storage Temperature	Tj,Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	90		V	IC=10μA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	90		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	6		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		50	nA	VCB=70V IE=0
Emitter Cutoff Current	IEBO		50	nA	VEB=4V IC=0
D.C. Current Gain	HFE	20			IC=100μA VCE=10V
		25			IC=1mA VCE=10V
		40	250		IC=10mA VCE=10V
		20			IC=100mA VCE=10V
Base-Emitter Saturation Voltage	VBE(sat)		0.9	V	IC=10mA IB=1mA
Collector-Emitter Saturation Voltage	VCE(sat)		0.5	V	IC=10mA IB=1mA

MICRO ELECTRONICS LTD. 美科有限公司
38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.
P.O. Box 9477, Kwun Tong. Tel: 3-430181-6, ~~3-893363, 3-892423, 3-898221~~ FAX: 3-410321

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